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DT09 Re PCT/PTO 16 SEP 2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

IONESCU et al

Atty. Ref.: 2590-100

Serial No. Unknown

Group:

National Phase of: PCT/CH02/00490

International Filing Date: 6 September 2002

Filed: Herewith

Examiner:

For: PROCESS FOR MANUFACTURING MEMS

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September 16, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO-1449, copies of non-U.S documents are enclosed. This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

Also enclosed is a copy of an International Search Report.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

IONESCU et al
Serial No. Unknown

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Respectfully submitted,

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INFORMATION DISCLOSURE CITATION

TY. DOCKET NO.

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(Use several sheets if necessary)

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS		FILING DATE IF APPROPRIATE
				CLASS	SUBCLASS	
	4,906,586	3/1990	Blackburn			
	5,262,000	11/1993	Welbourn et al			
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FOREIGN PATENT DOCUMENTS

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	Hoffman et al, "3D Structures with Piezoresistive Sensors in Standard CMOS", PROCEEDINGS OF THE WORKSHOP ON MICRO ELECTRICAL MECHANICAL SYSTEMS", January 29 - February 2, 1995, pp. 288-293.
	Devoe et al, "Surface Micromachined Piezoelectric Accelerometers (PIXLS)", JOURNAL OF MICROELECTROMECHANICAL SYSTEMS, IEEE INC., vol. 10, no. 2, June 2001, pp. 180-186.
	Chang et al, "Innovative micromachined microwave switch with very low insertion loss", SENSORS AND ACTUATORS A, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, vol. 79, no. 1, January 2000, pp. 71-75.
	Pott et al, "The suspended-gate MOSFET (SG-MOSFET): a modeling outlook for the design of RF MEMS switches and tunable capacitors", 2001 INTERNATIONAL SEMICONDUCTOR CONFERENCE, CAS 2001 PROCEEDINGS (CAT. NO. 01TH8547), CAS 2001 PROCEEDINGS. 2001 INTERNATIONAL SEMICONDUCTOR CONFERENCE, SINAIA, ROMANIA, 9-13 Oct. 2001, pp. 137-140.
	Zhang et al, "Temperature-controlled Kelvin microprobe", SENSORS AND ACTUATORS B, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, vol. B12, no. 3, 15 April 1993, pp. 175-180.
	Meister et al, "In situ control of the electrochemical gap height modification of a suspended gate field-effect transistor by capacitance -- voltage measurement technique", SENSORS AND ACTUATORS B, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, vol. 46, no. 3, 15 May 1998, pp. 226-235.

*Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.